

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
14 November 2024 (14.11.2024)



(10) International Publication Number
WO 2024/233704 A1

(51) International Patent Classification:
H01L 23/48 (2006.01)

(21) International Application Number:
PCT/US2024/028432

(22) International Filing Date:
08 May 2024 (08.05.2024)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
18/313,425 08 May 2023 (08.05.2023) US

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT,

(54) Title: STRUCTURE AND METHOD FOR POWER METAL LINES

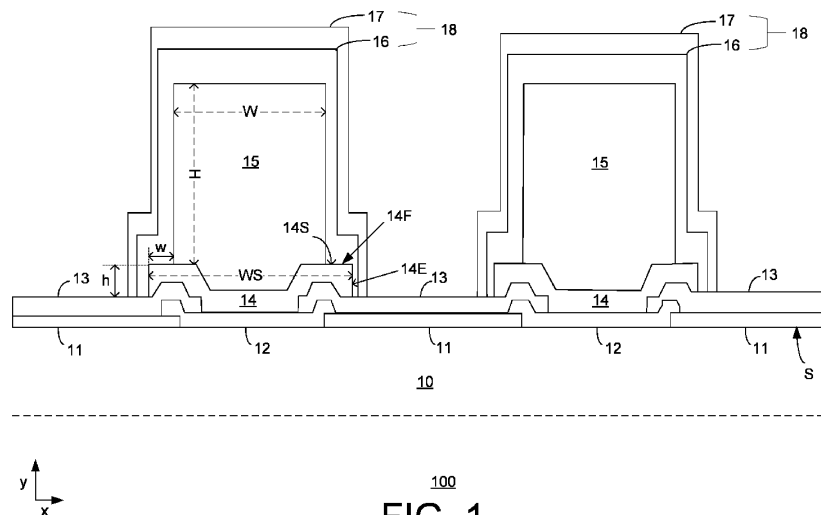


FIG. 1

(57) Abstract: A semiconductor device component includes a contact pad (12) disposed on a surface of a semiconductor substrate (10), a seed metal layer (14) disposed on the contact pad, and an interconnect disposed on the seed metal layer. The seed metal layer has a width that is greater than the width of the interconnect with a footer portion (14F) of the seed metal layer extending outside the width of the interconnect. The semiconductor device component further includes an etch-resistant protective structure (18) disposed on surfaces of the interconnect and the footer portion of the seed metal layer extending outside the width of the interconnect.

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LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE,
SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*